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4. (Currently Amended) A method of forming a lithographic template as claimed in claim 3 wherein the step of providing a charge dissipation layer adjacent the irradiation sensitive and directly patternable patterning layer includes forming the charge dissipation layer on an uppermost surface of the irradiation sensitive and directly patternable patterning layer, the irradiation sensitive and directly patternable patterning layer formed on the uppermost surface of the substrate.

5. (Original) A method of forming a lithographic template as claimed in claim 4 wherein the step of providing a charge dissipation layer includes forming the charge dissipation layer of a material chosen from the group consisting of: aluminum (Al), copper (Cu), polyaniline, and a charge dissipating conducting material.

6. (Currently Amended) A method of forming a lithographic template as claimed in claim 4 further including the step of forming a contrast enhancement layer between the substrate and the irradiation sensitive and directly patternable patterning layer.

7. (Original) A method of forming a lithographic template as claimed in claim 6 wherein the contrast enhancement layer is a material chosen from the group of chrome oxide (CrO), chrome nitride (CrN), titanium oxide (TiO), aluminum oxide (Al₂O₃), or aluminum nitride (AlN), or combinations thereof.